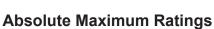
NPN Silicon Planar Switching Transistor 40VcEO, 800mA Ic

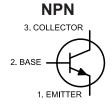






Description	Symbol	Value	Unit
Collector Emitter Voltage	VCEO	40	V
Collector Base Voltage	Vсво	75	V
Emitter Base Voltage	VEBO	6	V
Collector Current Continuous	Ic	800	mA
Power Dissipation at T _A = 25°C Derate above 25°C	Po	800 4.57	mW mW/°C
Power Dissipation at Tc = 25°C Derate Above 25°C	Po	3 17.15	W mW/°C
Operating and Storage Junction Temperature Range	Tj, Tstg	- 65 to +200	°C

RoHS Compliant



Electrical Characteristics: (TA = +25°C Unless otherwise specified)

Description	Symbol	Test Conditions	Min	Max	Unit
Collector -Emitter Voltage	VCEO	Ic = 10mA, I _B = 0	40	-	V
Collector Base Voltage	Vсво	Ic = 100μA, Iε = 0	75	-	V
Emitter Base Voltage	VEBO	Iε = 100μA, Ic = 0	6	-	V
Collector Cutoff Current	Ісво Ісех	VcB = 60V, IE = 0 VcB = 60V, IE = 0, TA = 150°C VcE = 60V, VEB = 3V	- - -	10 10 10	nΑ μΑ nΑ
Emitter-Cut off Current	ІЕВО	V _{EB} = 3V, I _C = 0	-	10	nA
Base-Cut off Current	IBL	Vce = 60V, Veb = 3V	-	20	nA
Collector Emitter Saturation Voltage	VCE(Sat)*	Ic = 150mA, I _B = 15mA Ic = 500mA, I _B = 50mA	-	0.3 1	V
Base Emitter Saturation Voltage	VBE(Sat)*	Ic = 150mA, Iв = 15mA Ic = 500mA, Iв = 50mA	-	0.6-1.2 2	V

Description	Symbol	Test Conditions	Values	Unit
DC Current Gain	hfe	Ic = 0.1mA, VcE = 10V Ic = 1mA, VcE = 10V Ic = 10mA, VcE = 10V TA = 55°C Ic = 10mA, VcE = 10V Ic = 150mA, VcE = 10V Ic = 150mA, VcE = 1V	>35 >50 >75 >35 100-300 >50	
		Ic = 500mA, VcE = 10V	>40	

NPN Silicon Planar Switching Transistor 40VcEO, 800mA Ic



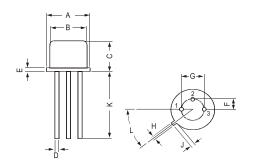
Description	Symbol	Test Conditions	Values	Unit
Dynamic Characteristics				
Small Signal Current Gain	hfe	ALL f = 1kHz Ic = 1mA, VcE = 10V Ic = 10mA, VcE = 10V	50 - 300 75-375	
Input Impedance	hie	Ic = 1mA, VcE = 10V Ic = 10mA, VcE = 10V	2 - 8 0.25-1.25	kΩ
Voltage Feedback Ratio	hre	Ic = 1mA, VcE = 10V Ic = 10mA, VcE = 10V	<8 <4	x10-4
Out put Admittance	hoe	Ic = 1mA, VcE = 10V Ic = 10mA, VcE = 10V	5 - 35 25 - 200	umhos
Collector Base Time Constant	rb'Cc	IE = 20mA, Vcв = 20V f = 31.8MHz	<150	ps
Real Part Common-Emitter High Frequency Input Impedance	Re(hie)	Ic = 20mA, Vce = 20V f=300MHz	<60	Ω
Noise Figure	NF	Ic = 100μA, Vcε = 10V Rs = 1kohms, f = 1kHz	<4	dB
Dynamic Characteristics			•	
Transistors Frequency	ft	Ic = 20mA, Vce = 20V f = 100MHz	>300	MHz
Out-Put Capacitance	Cob	Vcв = 10V, IE = 0 f = 100kHz	<8	pF
Input Capacitance	Cib	V _{EB} = 0.5V, I _C = 0 f = 100kHz	<25	pF
Switching Time	•		•	
Delay time	td	Ic = 150mA, Ів1 = 15mA	<10	ns
Rise time	tr	Vcc = 30V, VBE = 0.5V	<25	ns
Storage time	ts	Ic = 150mA	<225	ns
Fall time	tf	I _{B2} = 15mA, Vcc = 30V	<60	ns

^{*}Pulse Condition: Pulse Width=300µs, Duty Cycle=2%

NPN Silicon Planar Switching Transistor 40VcEo, 800mA Ic



TO-39 Metal Can Package



Dim.	Min.	Max.
Α	8.5	9.39
В	7.74	8.5
С	6.09	6.6
D	0.4	0.53
E	-	0.88
F	2.41	2.66

Dim.	Min.	Max.
G	4.82	5.33
Н	0.71	0.86
J	0.73	1.02
K	12.7	-
L	42 Deg.	48 Deg.

Dimensions: Millimetres

Part Number Table

Description	Part Number	
NPN Silicon Planar Switching Transistor, 40V, 800mA, TO-39	2N2219A	

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